

N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)			
30	0.0125 at V _{GS} = 10 V	55 ^d	18.2			
30	0.0163 at V _{GS} = 4.5 V	45 ^d	10.2			

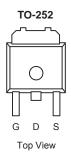
FEATURES

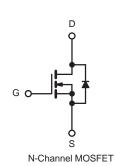
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- · Power Supply
 - Secondary Synchronous Rectification
- DC/DC Converter





ABSOLUTE MAXIMUM RATINGS T _C = 25 °C, unless otherwise noted						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V _{DS}	30	V			
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 25 °C	I _D	55 ^d	A		
Gontinadas Brain Gunerii (15 – 150 G)	T _C = 70 °C	'D	45 ^d			
Pulsed Drain Current	·	I _{DM}	165			
Avalanche Current		I _{AS}	34			
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	78	mJ		
Maritime Danie Diagination 4	T _C = 25 °C	P _D	55.5 ^b	W		
Maximum Power Dissipation ^a	T _A = 25 °C ^c	' D	2.7	VV		
Operating Junction and Storage Temperature Ra	inge	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	54	°C/W		
Junction-to-Case (Drain)	R _{thJC}	2.7]		

Notes:

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Package limited.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V_{DS} $V_{DS} = 0 \text{ V, } I_{D} = 250 \mu\text{A}$				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	55			Α
Drain-Source On-State Resistance ^a	_	V _{GS} = 10 V, I _D = 12 A		0.0125	0.0157	Ω
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A		0.0163	0.0179	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		100		S
Dynamic ^b						
Input Capacitance	C _{iss}			578		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 15 V, f = 1 MHz		364		
Reverse Transfer Capacitance	C _{rss}			210		
Total Gate Charge ^c	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 20 A		34	56	
Total Gate Charge				20.1	30.2	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$		6		IIC
Gate-Drain Charge ^c	Q _{gd}			5.7		
Gate Resistance	R _g	f = 1 MHz	0.4	2	4	Ω
Turn-On Delay Time ^c	t _{d(on)}			8	16	
Rise Time ^c	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega$		9	18	200
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		35	53	ns
Fall Time ^c	t _f			9	18	
Drain-Source Body Diode Ratings at	nd Characteri	stics T _C = 25 °C ^b				
Continuous Current	I _S				55	٨
Pulsed Current	I _{SM}				165	Α
Forward Voltage ^a	V _{SD}	I _F = 10 A, V _{GS} = 0 V		0.75	1.5	V
Reverse Recovery Time	t _{rr}			34	51	ns
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 10 A, dI/dt = 100 A/μs		2	3	Α
Reverse Recovery Charge	Q _{rr}			34	51	nC

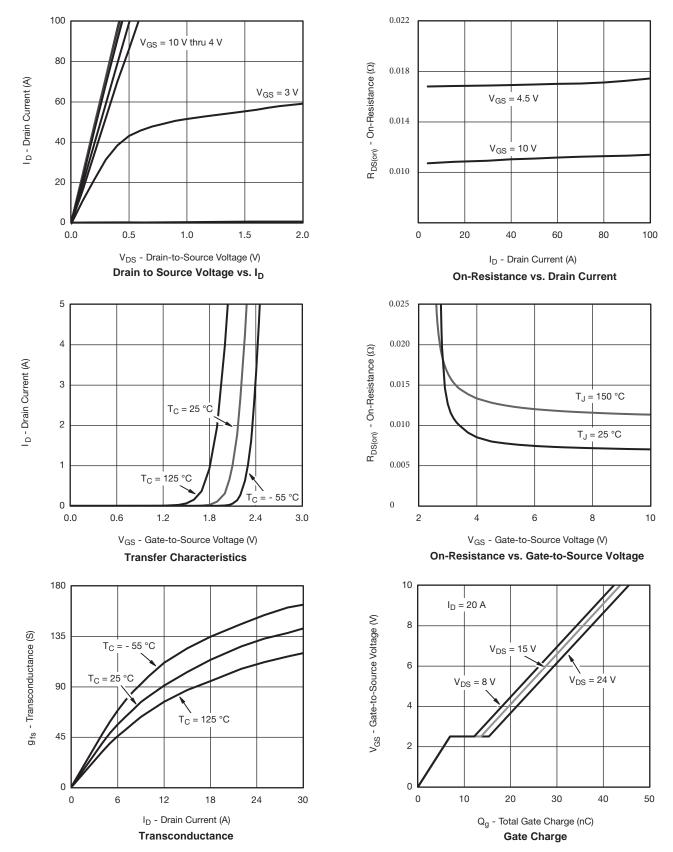
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

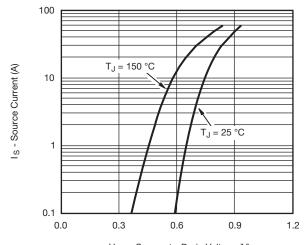
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

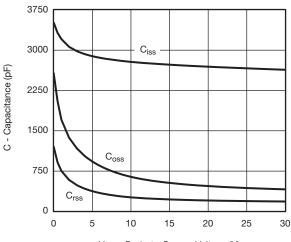


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



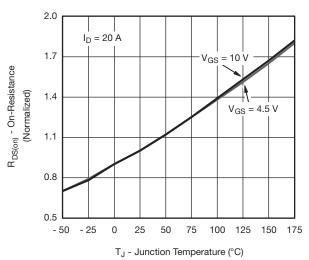
V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

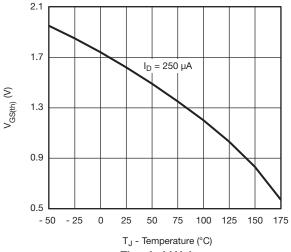


V_{DS} - Drain-to-Source Voltage (V)

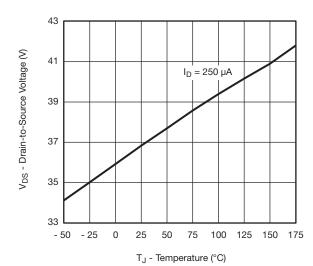
Capacitance



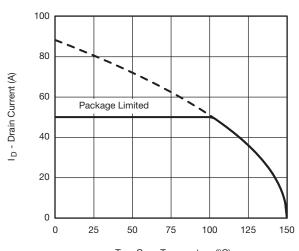
On-Resistance vs. Junction Temperature



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



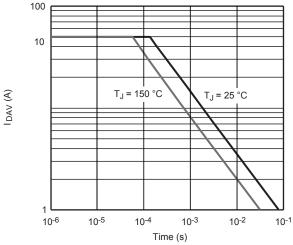
T_C - Case Temperature (°C)

Current Derating

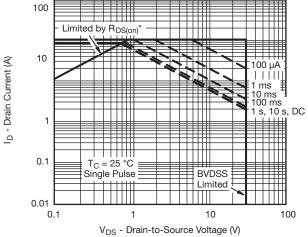
Din-Tek

www.din-tek.jp

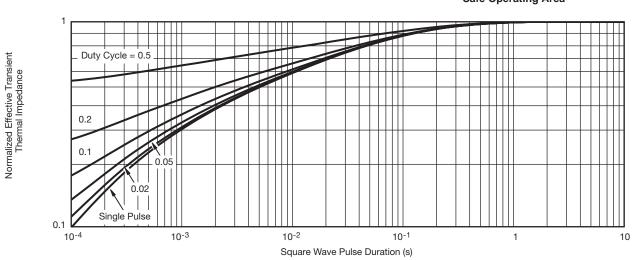
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Single Pulse Avalanche Current Capability vs. Time

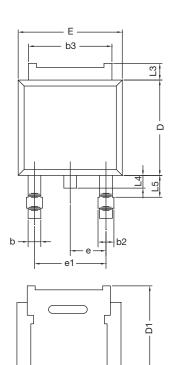


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified **Safe Operating Area**

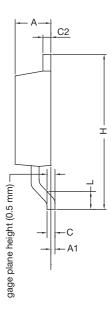


Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA CASE OUTLINE



E1



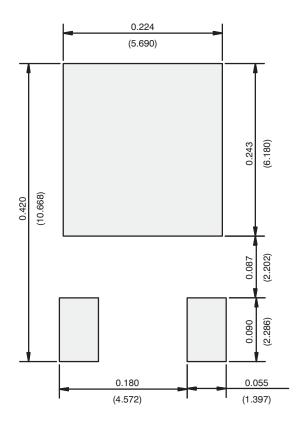
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
А	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.21	-	0.205	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28 BSC		0.090 BSC	
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.14	1.52	0.045	0.060
ECN: X12-0247-Rev. M, 24-Dec-12 DWG: 5347				

DWG: 5347

Note

• Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK(TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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